

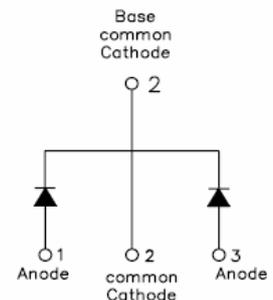
## MBR40150CT SCHOTTKY RECTIFIER

### Applications:

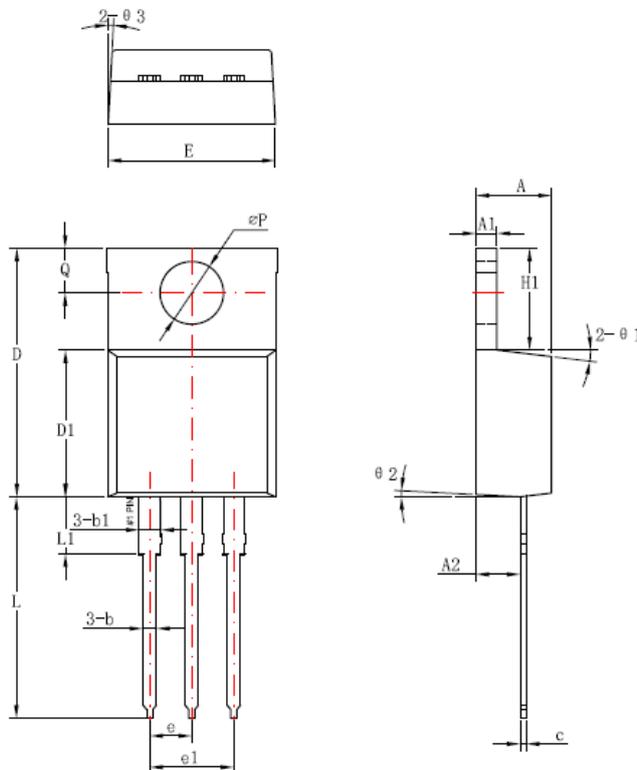
- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

### Features:

- 150 °C T<sub>J</sub> operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request



### Mechanical Dimensions: In mm

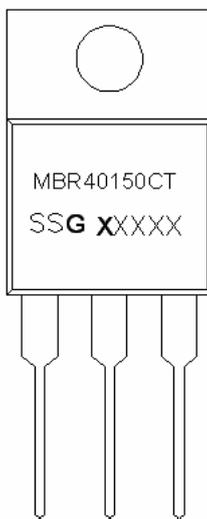


Symbol	Dimensions in millimeters		
	Min	Typical	Max
A	4.42	4.57	4.72
A1	1.17	1.27	1.37
A2	2.59	2.69	2.89
b	0.71	0.81	0.96
b1		1.27	
c	0.36	0.38	0.61
D	14.94	15.24	15.54
D1	8.85	9.00	9.15
E	10.01	10.16	10.31
e		2.54	
e1		5.06	
H1	6.04	6.24	6.44
L	12.7	13.56	13.78
L1		3.5	
ΦP	3.74	3.84	4.04
Q	2.54	2.74	2.94
θ1		7°	
θ2		3°	
θ3		4°	

### TO-220AB



**Marking Diagram:**



Where XXXXX is YYWWL

MBR = Device Type  
 40 = Forward Current (40A)  
 150 = Reverse Voltage (150V)  
 CT = Configuration  
 SSG = SSG  
 YY = Year  
 WW = Week  
 L = Lot Number

**Cautions:** Molding resin  
Epoxy resin UL:94V-0

**Ordering Information:**

Device	Package	Shipping
MBR40150CT	TO-220AB (Pb-Free)	50pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

**Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	$V_{RWM}$	-	150	V
Max. Average Forward	$I_{F(AV)}$	50% duty cycle @ $T_C=110^\circ\text{C}$ , rectangular wave form	20(per leg)	A
			40(Per device)	
Max. Peak One Cycle Non-Repetitive Surge Current (per leg)	$I_{FSM}$	8.3 ms, half Sine pulse	250	A



**Electrical Characteristics:**

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop (per leg)*	$V_{F1}$	@ 20A, Pulse, $T_J = 25\text{ }^\circ\text{C}$	0.95	V
	$V_{F2}$	@ 20 A, Pulse, $T_J = 125\text{ }^\circ\text{C}$	0.92	V
Max. Reverse Current at DC condition (per leg)	$I_{R1}$	@ $V_R = \text{rated } V_R$ $T_J = 25\text{ }^\circ\text{C}$	1.0	mA
Max. Reverse Current (per leg)*	$I_{R2}$	@ $V_R = \text{rated } V_R$ $T_J = 125\text{ }^\circ\text{C}$	15.0	mA
Non-Repetitive Avalanche Energy	$E_{AS}$	$T_J = 25\text{ }^\circ\text{C}$ , $I_{AS} = 2\text{ A}$ , $L = 1\text{ mH}$	2	mJ
Max. Junction Capacitance (per leg)	$C_T$	@ $V_R = 5\text{ V}$ , $T_C = 25\text{ }^\circ\text{C}$ $f_{SIG} = 1\text{ MHz}$	900	pF
Typical Series Inductance (per leg)	$L_S$	Measured lead to lead 5 mm from package body	8.0	nH
Max. Voltage Rate of Change	$dv/dt$	-	10,000	V/ $\mu\text{s}$

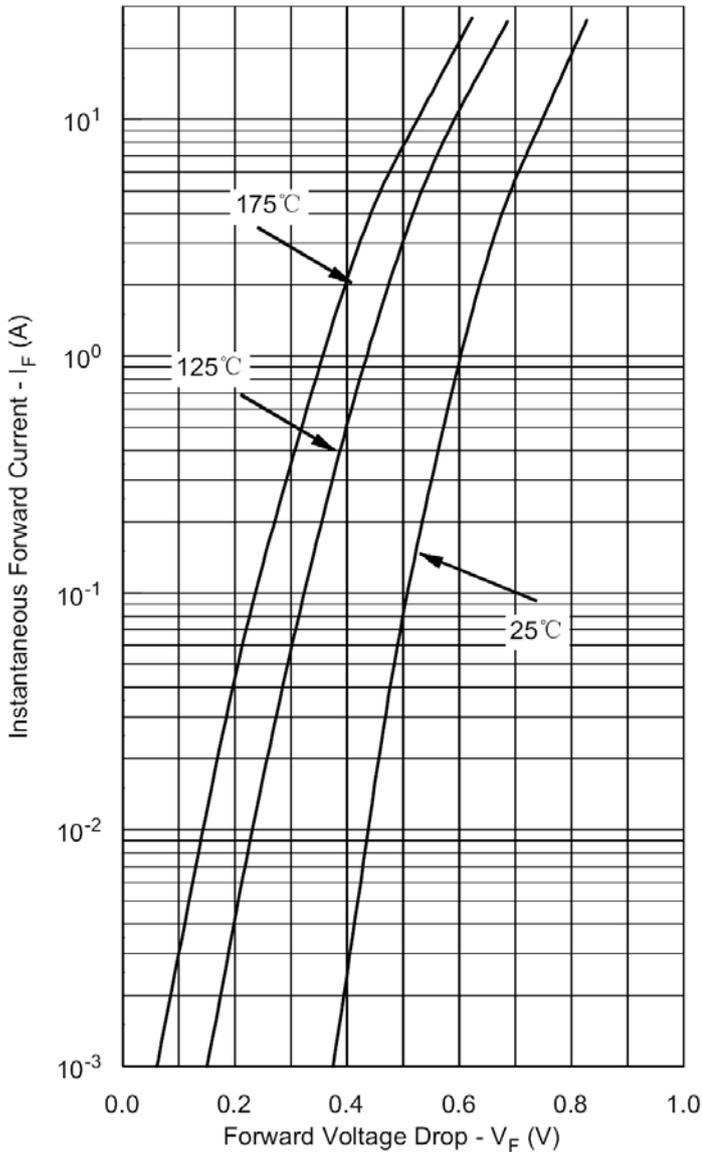
\* Pulse Width < 300 $\mu\text{s}$ , Duty Cycle <2%

**Thermal-Mechanical Specifications:**

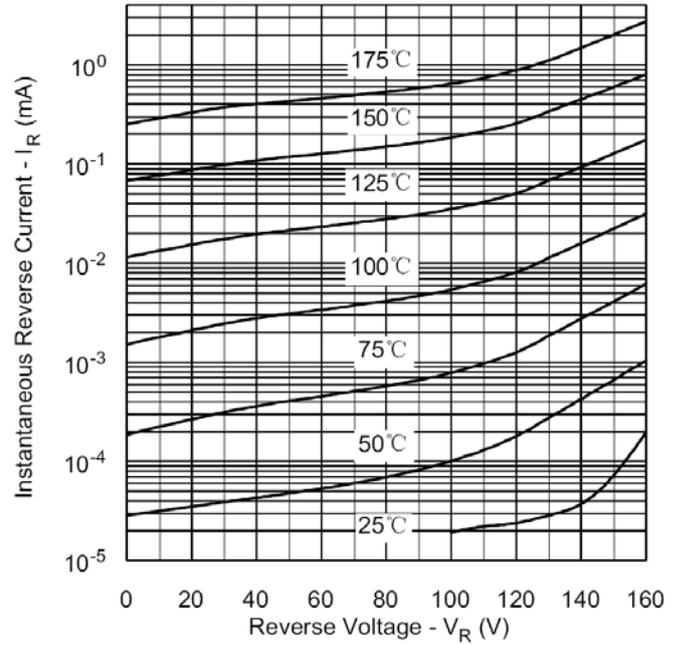
Characteristics	Symbol	Condition	Specification	Units
Max. Junction Temperature	$T_J$	-	-55 to +150	$^\circ\text{C}$
Max. Storage Temperature	$T_{stg}$	-	-55 to +150	$^\circ\text{C}$
Maximum Thermal Resistance Junction to Case (per leg)	$R_{\theta JC}$	DC operation	3.0	$^\circ\text{C/W}$
Approximate Weight	wt	-	2	g
Case Style	TO-220AB			



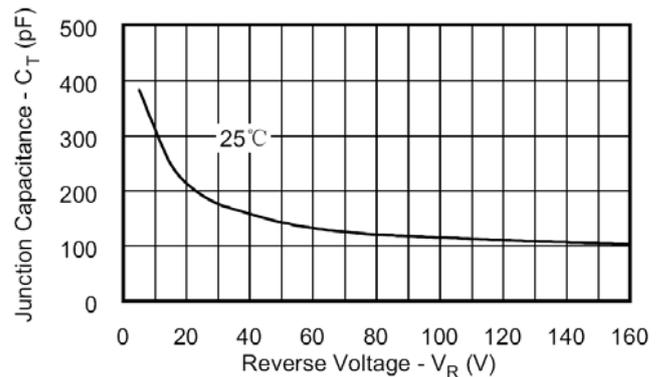
### Typical Forward Characteristics



### Typical Reverse Characteristics



### Typical Junction Capacitance



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